

DESCRIPTION

- Collector Current $-I_C = 16A$
- Collector-Emitter Saturation Voltage:
 $V_{CE(sat)} = 2.0V(\text{Max.}) @ I_C = 10A$
- Complement to Type BDV66/A/B/C

APPLICATIONS

- Designed for audio output stages and general amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

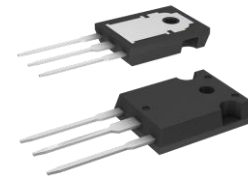
SYMBOL	PARAMETER	VALUE	UNIT	
V_{CBO}	Collector-Base Voltage	BDV67	80	V
		BDV67A	100	
		BDV67B	120	
		BDV67C	140	
V_{CEO}	Collector-Emitter Voltage	BDV67	60	V
		BDV67A	80	
		BDV67B	100	
		BDV67C	120	
V_{EBO}	Emitter-Base Voltage	5	V	
I_C	Collector Current-Continuous	16	A	
I_{CM}	Collector Current-Peak	20	A	
I_B	Base Current-Continuous	0.5	A	
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	175	W	
T_J	Junction Temperature	150	$^\circ C$	
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$	

THERMAL CHARACTERISTICS

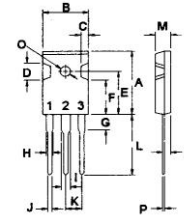
SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.625	$^\circ C/W$

PNP	NPN
BDV66	BDV67
BDV66A	BDV67A
BDV66B	BDV67B
BDV66C	BDV67C

16 AMPERE
 DARLINGTON
 COMPLEMENTARY SILICON
 POWER TRANSISTORS
 60-100 VOLTS
 125 WATTS



TO 247 (3)



**PIN 1. BASE
 2. COLLECTOR
 3. EMITTER**

DIM	MILLIMETERS	
	MIN	MAX
A	20.63	22.38
B	15.38	16.20
C	1.90	2.70
D	5.10	6.10
E	14.81	15.22
F	11.72	12.84
G	4.20	4.50
H	1.82	2.46
I	2.92	3.23
J	0.89	1.53
K	5.26	5.66
L	18.50	21.50
M	4.68	5.36
N	2.40	2.80
O	3.25	3.65
P	0.55	0.70



ELECTRICAL CHARACTERISTICS

$T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BDV67	$I_C=100\text{mA}; I_B=0$			V
		BDV67A				
		BDV67B				
		BDV67C				
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=10\text{A}; I_B=40\text{mA}$			2	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=10\text{A}; V_{CE}=3\text{V}$			2.5	V
I_{CEO}	Collector Cutoff Current	$V_{CE}=1/2V_{CEOmax}; I_B=0$			1	mA
I_{CBO}	Collector Cutoff Current	BDV67			5	mA
		BDV67A				
		BDV67B				
		BDV67C				
I_{CBO}	Collector Cutoff Current	$V_{CB}=V_{CBOmax}; I_E=0$			1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			5	mA
h_{FE}	DC Current Gain	$I_C=10\text{A}; V_{CE}=3\text{V}$	1000			
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1\text{MHz}$		300		pF

Switching times

t_{on}	Turn-on Time	$I_C=10\text{A}; I_{B1}=-I_{B2}=40\text{mA}; V_{CC}=12\text{V}$		1		μs
t_{off}	Turn-off Time			3.5		μs